Direct Growth of Sub-nm-Diameter SWNT Films on Si/SiO₂ Substrates by Alcohol Catalytic Chemical Vapor Deposition

Benjamin K. Wang,^{1,2} Hua An,¹ Kehang Cui,¹ & Shigeo Maruyama¹

¹Department of Mechanical Engineering, The University of Tokyo, Tokyo 113-8656, Japan

²Department of Chemical and Biomolecular Engineering and NanoJapan: International Research Experience for Undergraduates Program, Rice University, Houston, TX 77005, United States

Due to their unique and tunable properties, single-walled carbon nanotubes (SWNTs) possess excellent potential for applications in the fields of nanotechnology, electronics, and optics. Perhaps the most sought after objective of SWNT research is their chirality-specific growth. SWNTs possess unique structure-function relationships that are determined by their chiral properties—nanotube diameter and wrapping angle—which allow them to exhibit either metallic or semiconducting properties. In this study, we demonstrate the diameter modulation of SWNTs grown by alcohol catalytic chemical vapor deposition (ACCVD) on Si/SiO₂ substrates. Importantly, compared to bulk gasphase synthesized nanotubes, the direct growth of SWNTs on flat substrates is advantageous because it allows for the immediate use of grown SWNTs in nanodevice applications. We show temperature-dependence studies of SWNTs grown from Co/Mo and Co/Cu bimetallic catalysts, and then shift our focus to Co/Cu-grown nanotubes. which revealed efficient growth of sub-nanometer SWNTs. Radial breathing mode (RBM) frequencies of resonant Raman scattering and scanning electron microscopy (SEM) indicated the synthesis of thin film networks characterized by sub-nanometer SWNTs. Our results suggest that lower temperatures favor smaller diameter SWNTs. Moreover, we observed decreasing SWNT diameters as a function of reducing the total feedstock pressure. This trend suggests that higher partial pressures of ethanol (high feedstock supply rate) poison smaller-diameter catalyst nanoparticles, thus reducing the population of small diameter nanotubes. We anticipate that these results will have wideranging implications for the highly desired diameter-specific growth of SWNTs. Furthermore, our sub-nanometer SWNTs have promising potential for use in CNT-Si and CNT-Perovskite solar cells.

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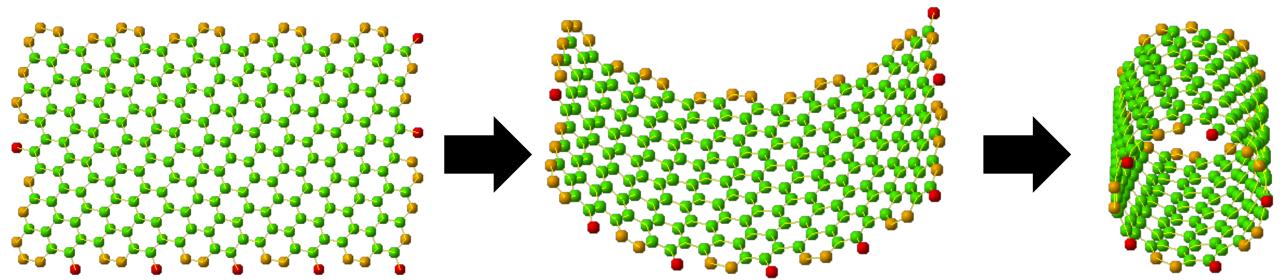
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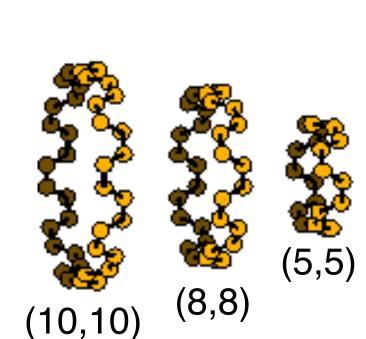
Introduction

Single-walled Carbon Nanotubes



Rolled up graphene sheet (planar honeycomb sp² hybridized C); high aspect-ratio1

Chirality



Geometry of the nanotube can be defined by the chiral vector (n,m) of the hexagonal lattice¹

Different chirality's result in different SWNT diameters¹

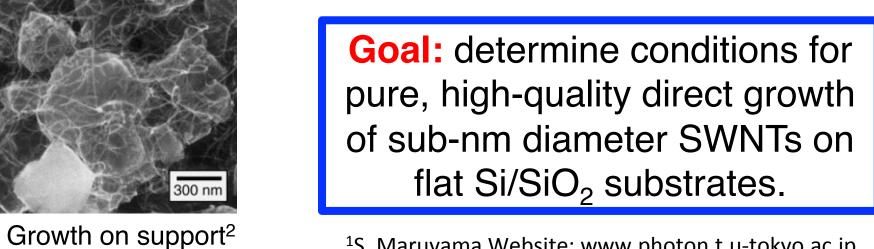
Nanodevice Applications

Unique properties:

- Mechanical strength
- Semiconducting or metallic

Optical absorption

Ar/H₂ Ar



of sub-nm diameter SWNTs on flat Si/SiO₂ substrates.

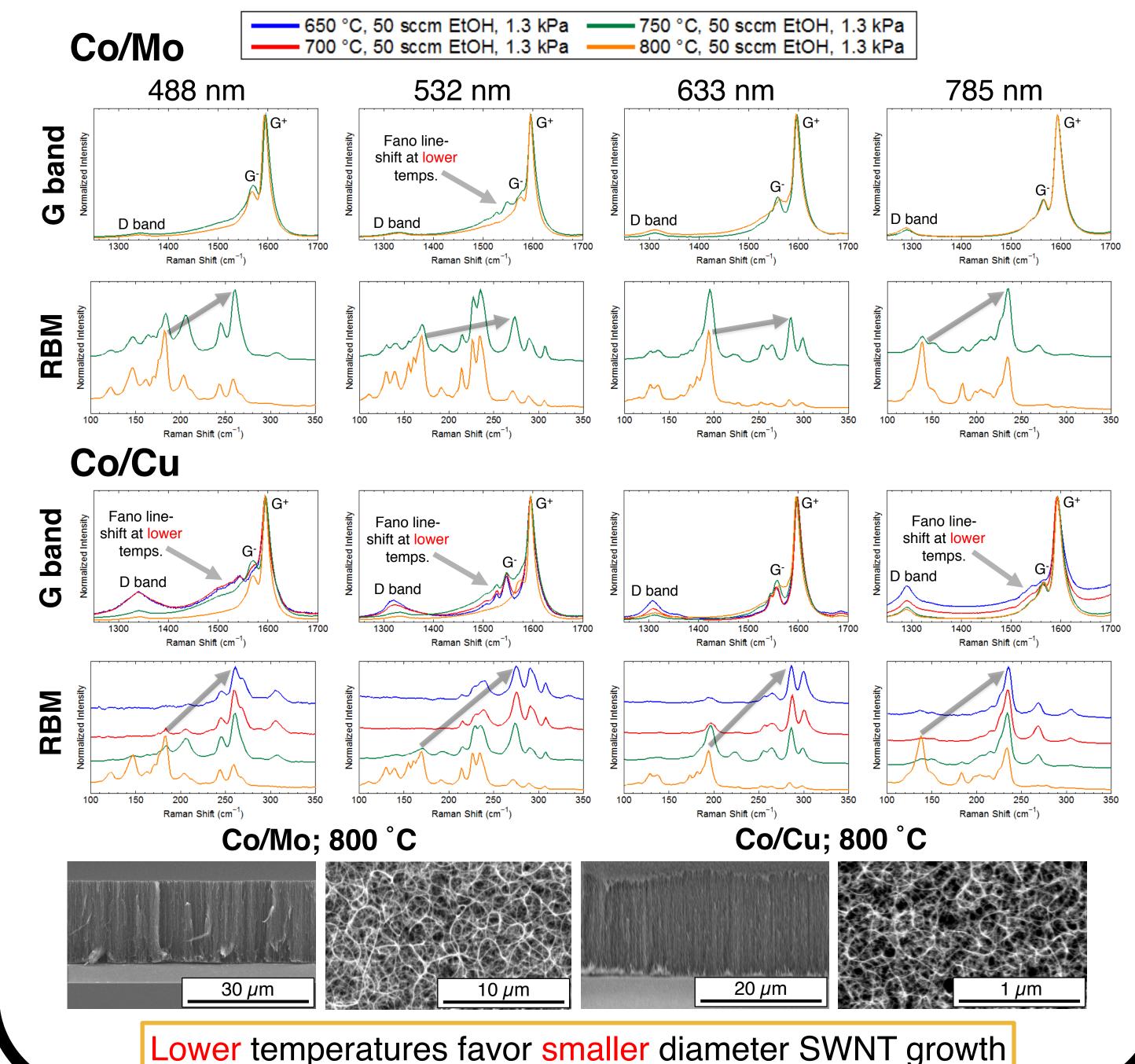
¹S. Maruyama Website; www.photon.t.u-tokyo.ac.jp

Methods

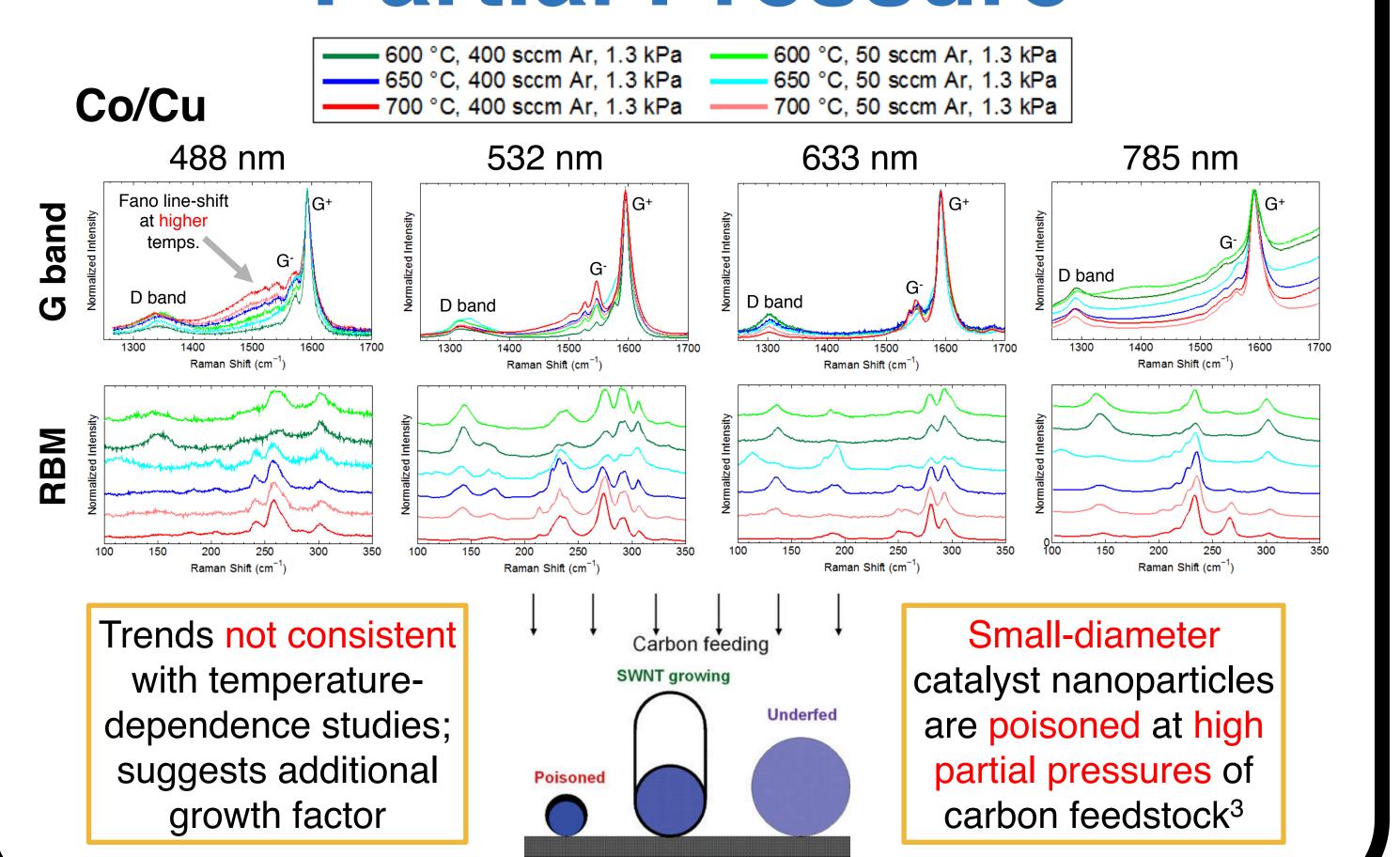
Alcohol Catalytic Chemical Vapor Deposition²

Direct synthesis on Si/SiO₂ substrate allows for immediate use in nanodevices; however, less control over catalyst size and distribution—difficult to produce high quality sub-nm SWNTs Growth on substrate

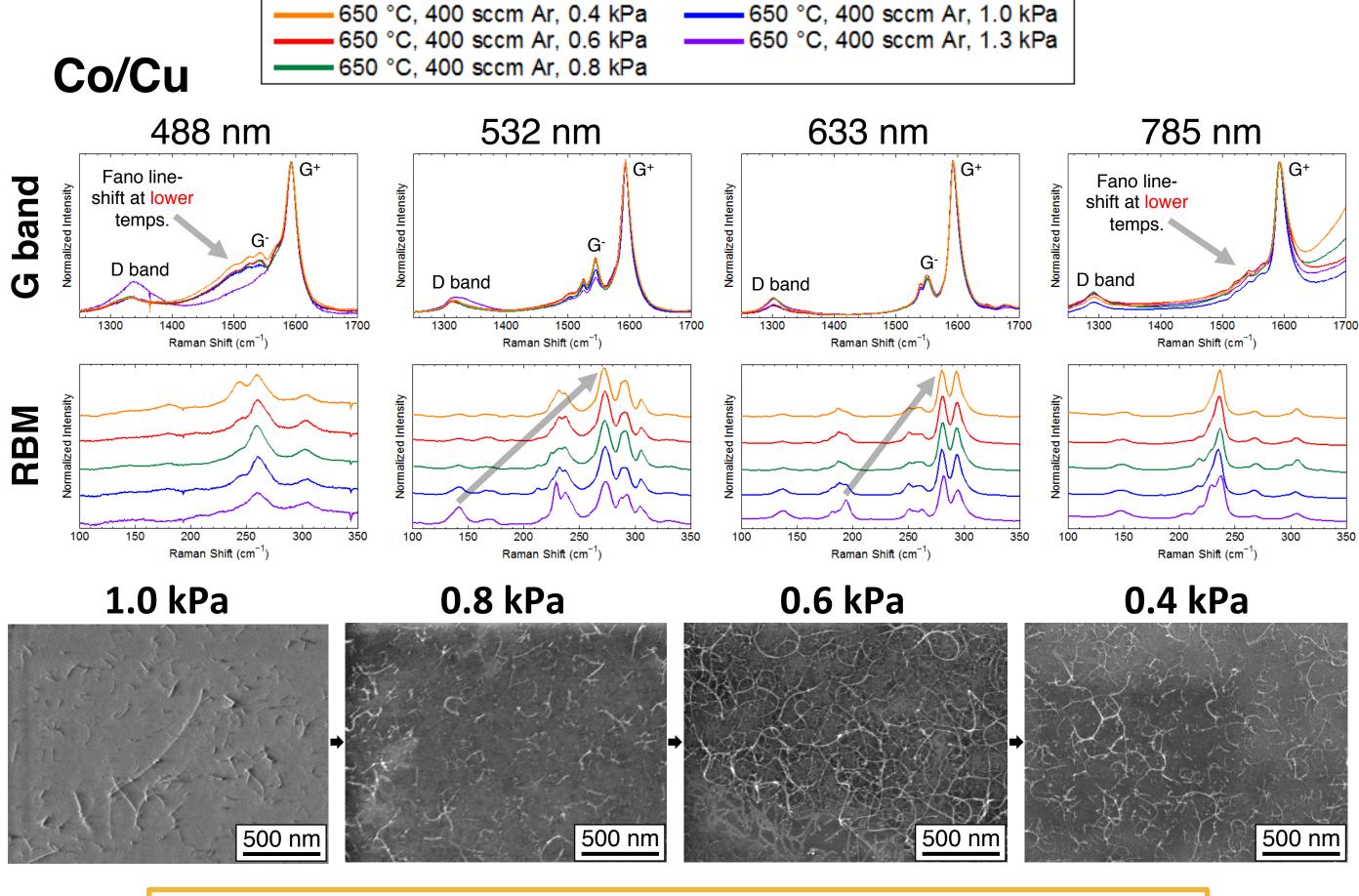
Temperature



Partial Pressure

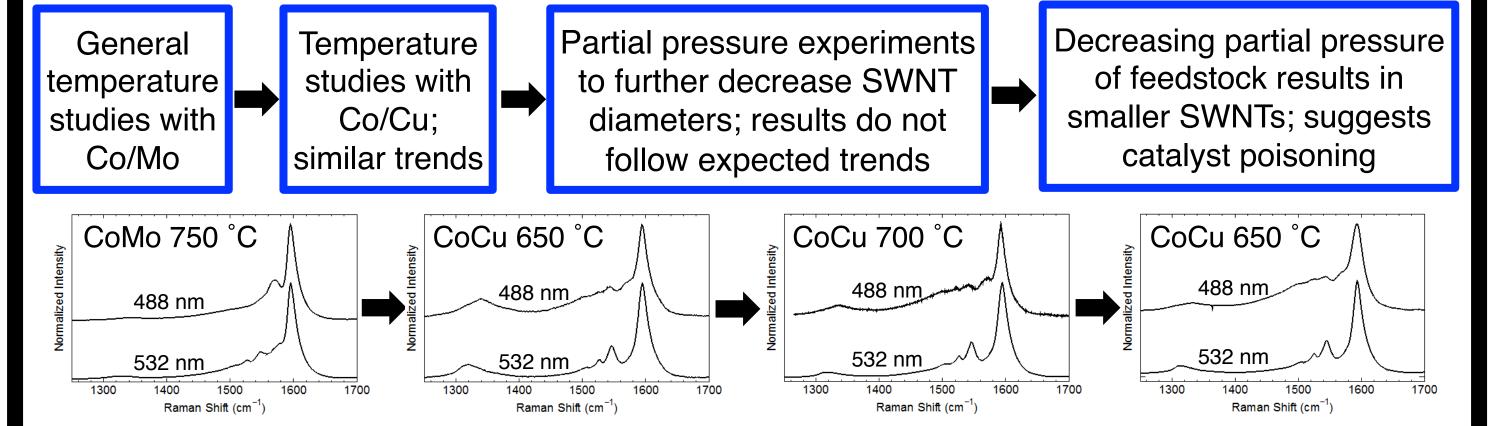


Total Pressure



Decreasing partial pressures of carbon feedstock results in thin-film networks characterized by sub-nm SWNTs

Conclusion & Future



- ~0.8-0.9 nm diameter SWNTs synthesized from Co/Cu
 - Semiconducting: (10,0), (9,2), (6,5), (7,5), (8,3)
 - Metallic: (7,7), (8,5), (12,1), (10,5)
- SWNT diameter further decreases as feedstock partial pressure decreases
- Decrease EtOH total pressure by several orders of magnitude while holding partial pressure constant
 - 1.0 kPa; 1.0 kPa; 0.1 kPa, 0.01 kPa
- Use sub-nm SWNTs for various nanodevice applications
 - CNT-Si and CNT-Perovskite solar cells

Acknowledgements

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Reduce and anneal Dip-coat Flow mixture of EtOH Characterize clean Si/SiO₂ metal oxide catalyst (feedstock) and Ar samples with at high temperature gas over Si/SiO₂ substrate with SEM, Raman metal catalyst with Ar/H₂ for 40 min substrate for 5 min Spectroscopy **Electric Furnace** Quartz Tube Pressure Substrate ¹Pressure Gauge Parameters to alter: Metal catalyst: Co/Mo vs. Co/Cu Reduction/growth temperature EtOH/Ar flow ratios

Total growth pressure

²Maruyama, S.; Kojima, R.; Miyauchi, Y.; Chiashi, S.; Kohno, M. *Chem Phys Lett* **2002**, *360*, 229.